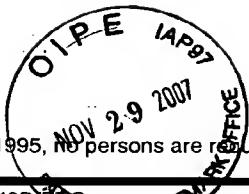


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Application Number	-Unassigned 10590485
Filing Date	04/02/08
First Named Inventor	Igor BARGATIN et al.
Group Art Unit	Unassigned 2855
Examiner Name	Unassigned M. Noori

Attorney Docket Number 049411-0340

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
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/MN/	A30	WO	2003/095616	A2	California Inst. of Tech.	11/20/2003		
/MN/	A31	WO	2003/095617	A2	California Inst. of Tech.	11/20/2003		
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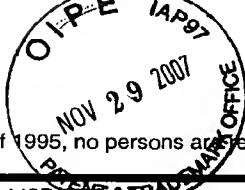
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NON PATENT LITERATURE DOCUMENTS

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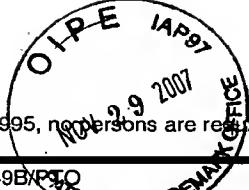
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NON PATENT LITERATURE DOCUMENTS

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